

## GaAs Molecular Beam Epitaxy Monolithic Power Amplifiers at U-Band (1989 [MCS])

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The design, fabrication, and measurements for 44-GHz band molecular beam epitaxy (MBE) monolithic power amplifiers are described. A five-stage balanced amplifier provided a linear gain of 15.1 dB and maximum output power of 500 mW at 42.5 GHz. These results may represent the highest power and gain achieved from a MIMIC in the 44-GHz band.

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